

# MEM13003T

## **BIPOLAR TRANSISTOR CHIP MEM13003T**

#### **General Description**

Switching regulator application.

High voltage and high speed.

Switching application.

#### Pin Configuration

- Pin Description
- 1 EMITTER (E)
- 2 COLLECTOR (C)
- 3 BASE (B)

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### Features

High Collector Voltage:700V

Package:TO-92

## Maximum Ratings(Ta=25)

Characteristics		Symbol	Rating	Unit	
Collector-Base Voltage		V <sub>CBO</sub>	700	V	
Collector-Emitter Voltage		V <sub>CEO</sub>	400	V	
Emitter-Base Voltage		V <sub>EBO</sub>	9	V	
Collector Current	DC	Ι <sub>C</sub>	1.5	Δ	
	Pulse	I <sub>CP</sub>	3	~	
Base Current		I <sub>B</sub>	0.75	А	
Collector Power Dissipation (Ta=25)		Pc	0.9	W	
Junction Temperature		Tj	150		
Storage Temperature Range		T <sub>stg</sub>	-55 ~ 150		

#### Electrical Characteristics (Ta=25)

Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
V <sub>(BR)CBO</sub>	I <sub>C</sub> =1mA,I <sub>E</sub> =0	700	-	-	V	
V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA,I <sub>B</sub> =0	400	-	-	V	
V <sub>(BR)EBO</sub>	I <sub>E</sub> =1mA,I <sub>C</sub> =0	9	-	-	V	
I <sub>CBO</sub>	V <sub>CB</sub> =700V,I <sub>E</sub> =0	-	-	100	μA	
I <sub>CEO</sub>	V <sub>CE</sub> =400V,I <sub>B</sub> =0	-	-	50	μA	
I <sub>EBO</sub>	V <sub>EB</sub> =7V,I <sub>C</sub> =0	-	-	10	μA	
h	V <sub>CE</sub> =10V, I <sub>C</sub> =0.2A	20	-	40	-	
I IFE	V <sub>CE</sub> = 5V, I <sub>C</sub> =0.5A	15	-	40	-	
V <sub>BE(sat)</sub>	I <sub>C</sub> =0.5A,I <sub>BE</sub> =0.1A	-	-	1	V	
	I <sub>C</sub> =1A,I <sub>BE</sub> =0.25A	-	-	1.2		
V <sub>CE(sat)</sub>	I <sub>C</sub> =1A,I <sub>BE</sub> =0.25A	-	-	1	V	
	I <sub>C</sub> =1.5A,I <sub>BE</sub> =0.5	-	-	3	v	



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## Package Information

### Package Type:TO-92



Symbol	Millimeters			
Symbol	Min.	Max.		
А	3.4	3.8		
В	0.3	0.5		
С	4.4	4.8		
D	4.4	4.8		
E	0.9	1.5		
е	1.17	1.37		
e1	2.39	2.69		
L	12	16		



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